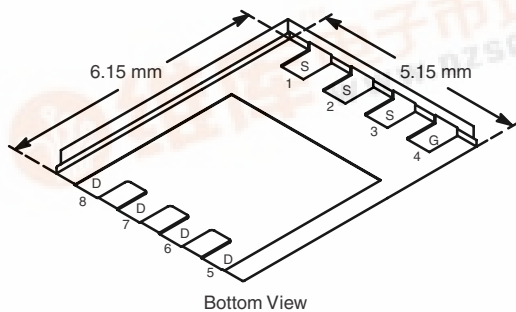


N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^g	Q _g (Typ.)
200	0.070 at V _{GS} = 10 V	25	34
	0.076 at V _{GS} = 6 V	24	

PowerPAK SO-8



Bottom View

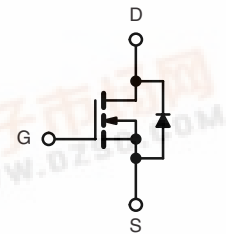
FEATURES

- Halogen-free
- TrenchFET[®] Power MOSFET
- Low Thermal Resistance PowerPAK[®] Package
- 100 % R_g Tested
- 100 % UIS Tested

RoHS
COMPLIANT

APPLICATIONS

- Primary Side Switch
- Industrial



N-Channel MOSFET

Ordering Information: Si7172DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	200	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	25
		T _C = 70 °C	20
		T _A = 25 °C	5.9 ^{b, c}
		T _A = 70 °C	4.8 ^{b, c}
Pulsed Drain Current	I _{DM}	30	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	4.5 ^{b, c}
Avalanche Current	I _{AS}	15	mJ
Single-Pulse Avalanche Energy	E _{AS}	11.25	
Maximum Power Dissipation	P _D	T _C = 25 °C	96
		T _C = 70 °C	61.5
		T _A = 25 °C	5.4 ^{b, c}
		T _A = 70 °C	3.5 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	18	23	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	1.0	1.5	

Notes:

- Package limited.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- See Solder Profile (<http://www.vishay.com/ppg?73461>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 65 °C/W.
- Based on T_C = 25 °C.



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	200			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		207		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-9.1		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5.9\text{ A}$		0.058	0.070	Ω
		$V_{GS} = 6\text{ V}, I_D = 5.7\text{ A}$		0.063	0.076	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 5.9\text{ A}$		19		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2250		pF
Output Capacitance	C_{oss}			115		
Reverse Transfer Capacitance	C_{rss}			61		
Total Gate Charge	Q_g	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 5.9\text{ A}$		51	77	nC
			$V_{DS} = 100\text{ V}, V_{GS} = 6\text{ V}, I_D = 5.9\text{ A}$		34	
Gate-Source Charge	Q_{gs}			14		
Gate-Drain Charge	Q_{gd}		15.5			
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.0	2.0	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 20.8\text{ }\Omega$ $I_D \cong 4.8\text{ A}, V_{GEN} = 6\text{ V}, R_g = 1\text{ }\Omega$		22	33	ns
Rise Time	t_r			12	18	
Turn-Off Delay Time	$t_{d(off)}$			24	36	
Fall Time	t_f			10	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 20.8\text{ }\Omega$ $I_D \cong 4.8\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		15	23	
Rise Time	t_r			11	20	
Turn-Off Delay Time	$t_{d(off)}$			26	39	
Fall Time	t_f			9	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			30	A
Pulse Diode Forward Current ^a	I_{SM}				30	
Body Diode Voltage	V_{SD}	$I_S = 4.8\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 4.8\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		80	120	ns
Body Diode Reverse Recovery Charge	Q_{rr}			275	413	nC
Reverse Recovery Fall Time	t_a			60		ns
Reverse Recovery Rise Time	t_b			20		

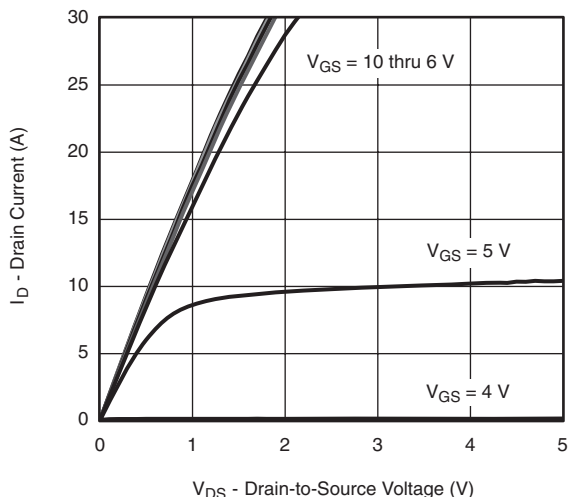
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

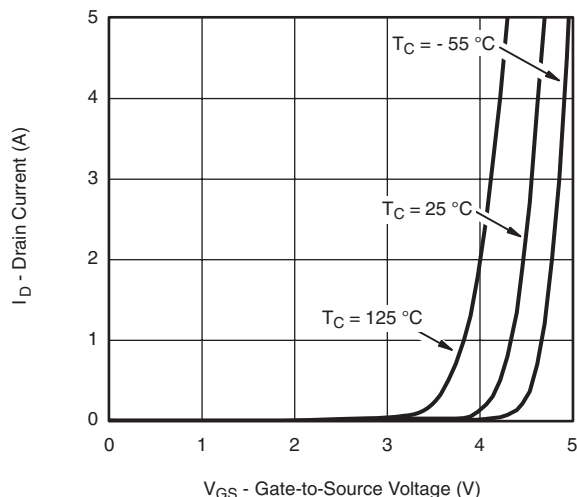
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



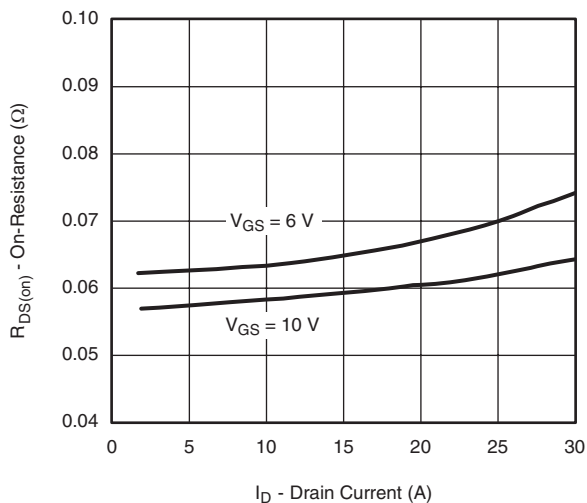
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



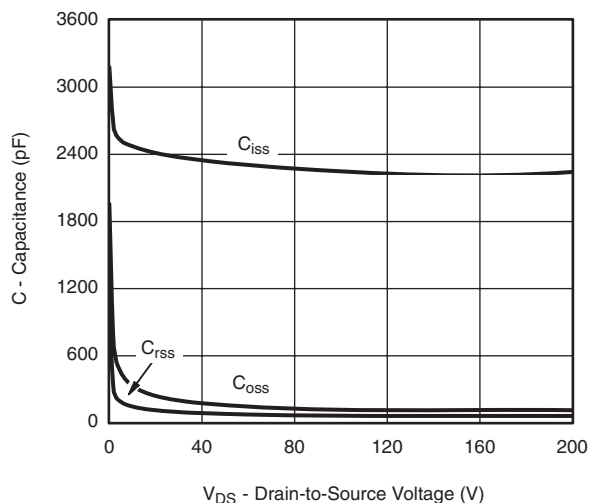
Output Characteristics



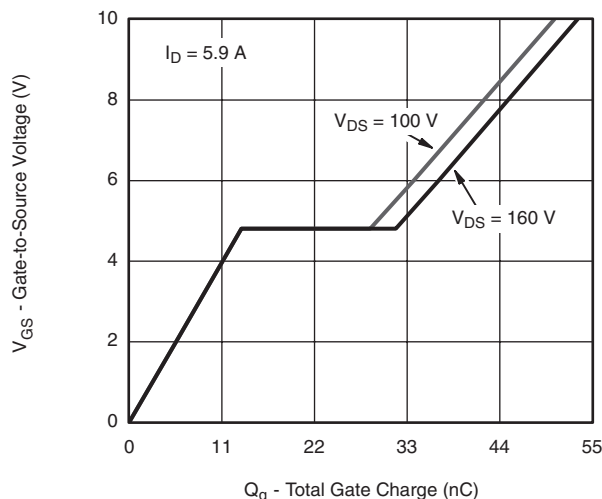
Transfer Characteristics



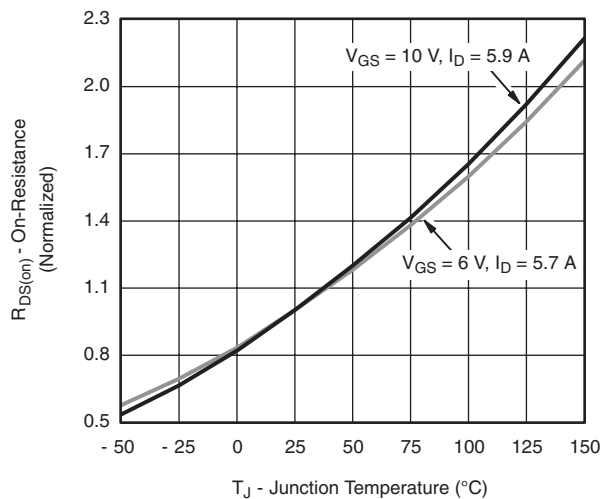
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



Gate Charge



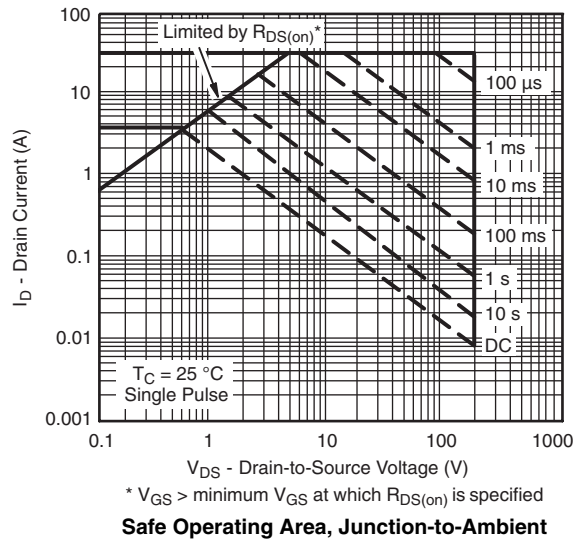
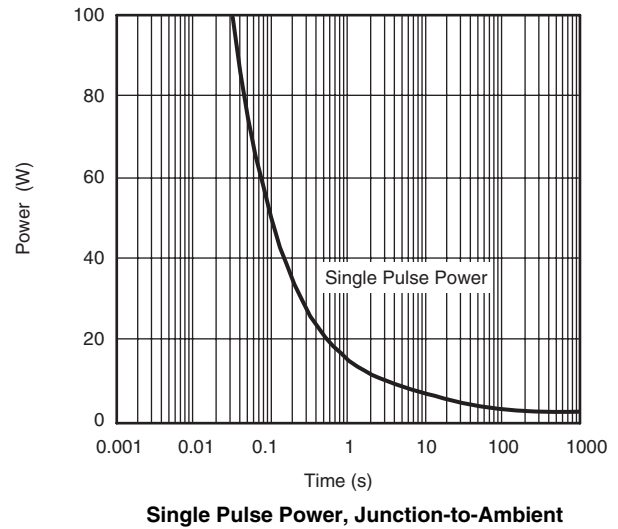
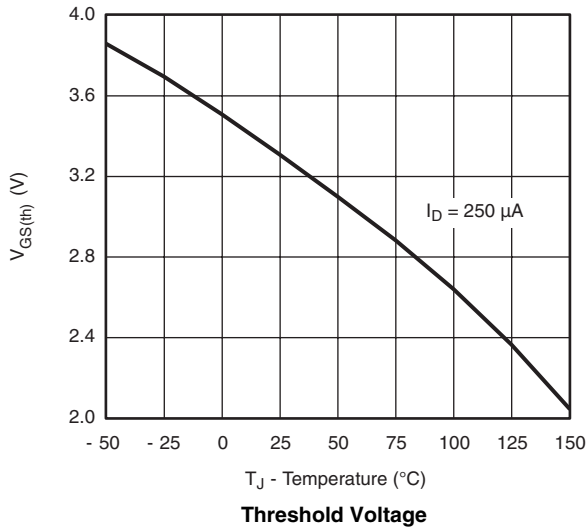
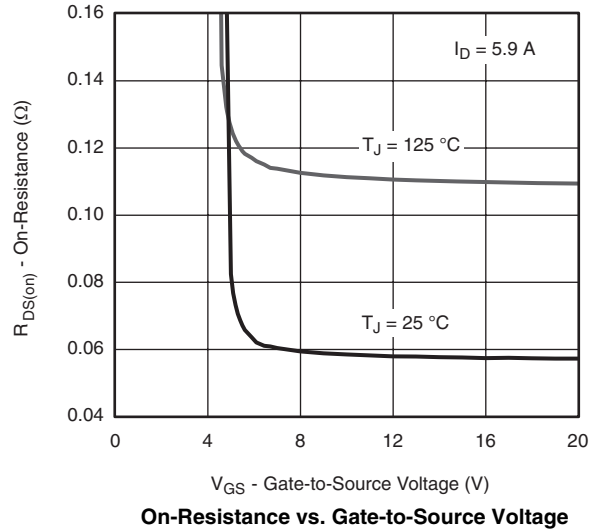
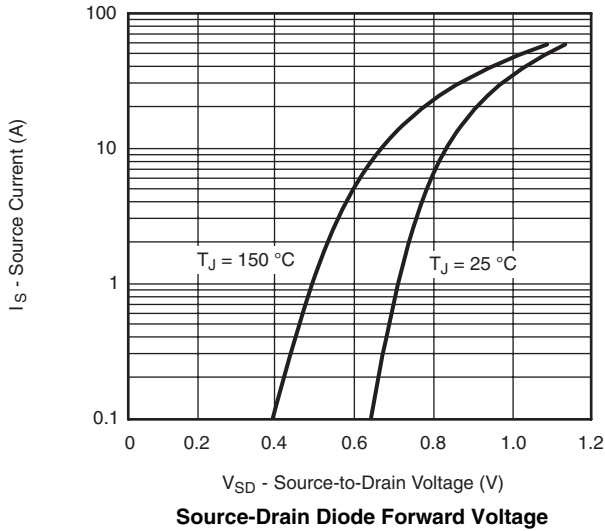
On-Resistance vs. Junction Temperature

Si7172DP

上海"Si7172DP"供应商
Vishay Siliconix

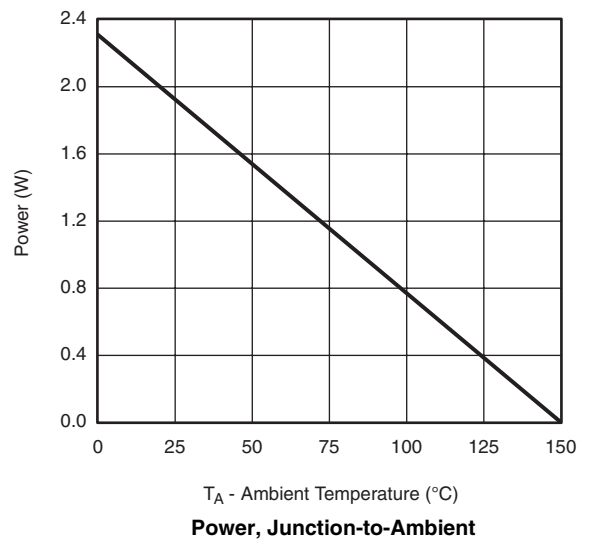
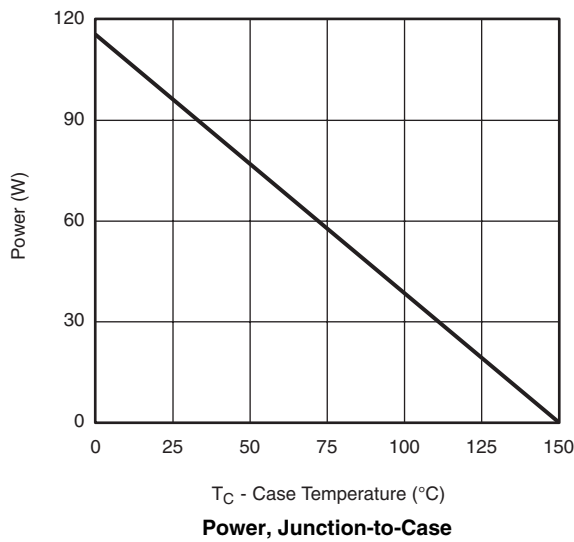
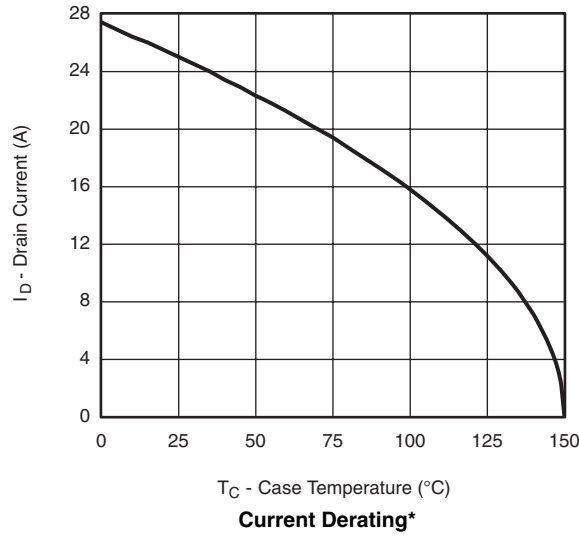


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



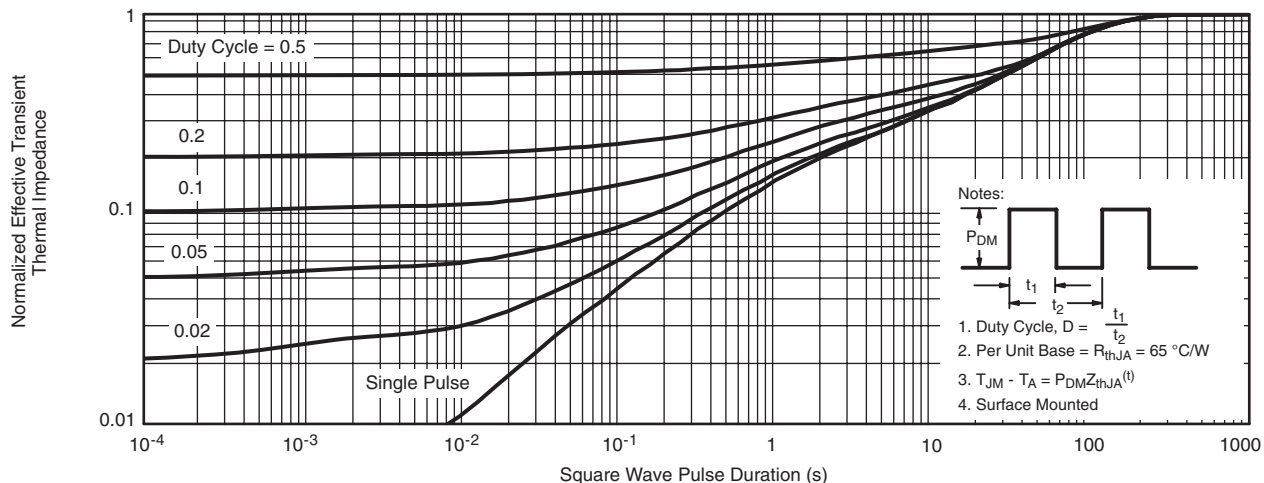
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si7172DP

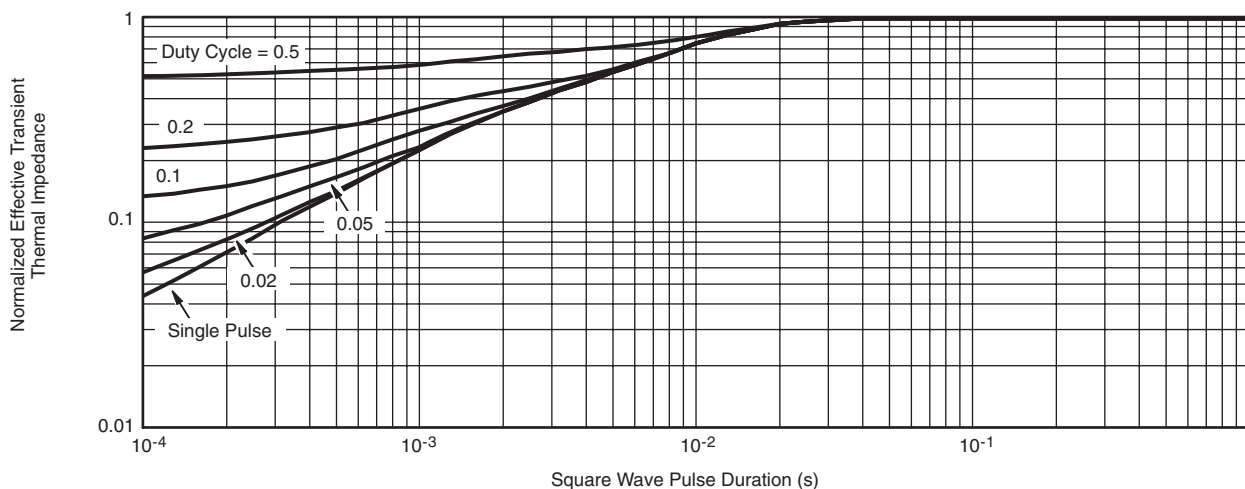


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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